

Nasir Alfaraj

List of Publications by Year in descending order

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papers

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27
all docs

27
docs citations

27
times ranked

709
citing authors

#	ARTICLE	IF	CITATIONS
1	III-nitride nanowires on unconventional substrates: From materials to optoelectronic device applications. Progress in Quantum Electronics, 2018, 61, 1-31.	7.0	76
2	Deep-Ultraviolet Photodetection Using Single-Crystalline $\text{In}^{2-}\text{Ga}^{2-}\text{O}^{3-}/\text{NiO}$ Heterojunctions. ACS Applied Materials & Interfaces, 2019, 11, 35095-35104.	8.0	75
3	Photoinduced entropy of InGaN/GaN p-i-n double-heterostructure nanowires. Applied Physics Letters, 2017, 110, .	3.3	50
4	Free-space optical channel characterization and experimental validation in a coastal environment. Optics Express, 2018, 26, 6614.	3.4	36
5	Deep-ultraviolet integrated photonic and optoelectronic devices: A prospect of the hybridization of group III nitrides, III oxides, and two-dimensional materials. Journal of Semiconductors, 2019, 40, 121801.	3.7	33
6	Nonplanar Nanoscale Fin Field Effect Transistors on Textile, Paper, Wood, Stone, and Vinyl <i>via</i> Soft Material-Enabled Double-Transfer Printing. ACS Nano, 2015, 9, 5255-5263.	14.6	26
7	Influence of TMAI preflow on AlN epitaxy on sapphire. Applied Physics Letters, 2017, 110, 192106.	3.3	22
8	The effect of turbulence on NLOS underwater wireless optical communication channels [Invited]. Chinese Optics Letters, 2019, 17, 100013.	2.9	21
9	Functional integrity of flexible n-channel metal oxide semiconductor field-effect transistors on a reversibly bistable platform. Applied Physics Letters, 2015, 107, .	3.3	18
10	Observation of piezotronic and piezo-phototronic effects in n-InGaN nanowires/Ti grown by molecular beam epitaxy. Nano Energy, 2018, 54, 264-271.	16.0	18
11	Single-Crystalline All-Oxide $\text{In}^{2-}\text{Ga}^{2-}\text{O}^{3-}$ Heterostructures for Deep-Ultraviolet Photodetection. ACS Applied Materials & Interfaces, 2020, 12, 53932-53941.	8.0	14
12	Out-of-Plane Strain Effects on Physically Flexible FinFET CMOS. IEEE Transactions on Electron Devices, 2016, 63, 2657-2664.	3.0	13
13	Structural properties, crystal quality and growth modes of MOCVD-grown AlN with TMAI pretreatment of sapphire substrate. Journal Physics D: Applied Physics, 2017, 50, 395101.	2.8	13
14	Thermodynamic photoinduced disorder in AlGaIn nanowires. AIP Advances, 2017, 7, .	1.3	12
15	Enhanced electro-optic performance of surface-treated nanowires: origin and mechanism of nanoscale current injection for reliable ultraviolet light-emitting diodes. Optical Materials Express, 2019, 9, 203.	3.0	11
16	Enhanced cooling in mono-crystalline ultra-thin silicon by embedded micro-air channels. AIP Advances, 2015, 5, 127115.	1.3	10
17	On-Chip Hyperuniform Lasers for Controllable Transitions in Disordered Systems. Laser and Photonics Reviews, 2020, 14, 1800296.	8.7	10
18	Heteroepitaxial $\text{In}^{2-}\text{Ga}^{2-}\text{O}^{3-}$ on Conductive Ceramic Templates: Toward Ultrahigh Gain Deep-Ultraviolet Photodetection. Advanced Materials Technologies, 2021, 6, 2100142.	5.8	10

#	ARTICLE	IF	CITATIONS
19	Revealing microstructure and dislocation behavior in BAlN/AlGaN heterostructures. Applied Physics Express, 2018, 11, 011001.	2.4	8
20	Out-of-plane strain effect on silicon-based flexible FinFETs. , 2015, , .		5
21	Timeâ€“Energy Quantum Uncertainty: Quantifying the Effectiveness of Surface Defect Passivation Protocols for Low-Dimensional Semiconductors. ACS Applied Electronic Materials, 2020, 2, 409-418.	4.3	4
22	Silicon-integrated monocrystalline oxideâ€“nitride heterostructures for deep-ultraviolet optoelectronics. Optical Materials Express, 2021, 11, 4130.	3.0	4
23	Ultra-high density out-of-plane strain sensor 3D architecture based on sub-20 nm PMOS FinFET. , 2015, , .		3
24	Functional integrity and stable high-temperature operation of planarized ultraviolet-A Al _x Ga _{1-^x} N/Al _y Ga _{1-^y} N multiple-quantum-disk nanowire LEDs with charge-conduction promoting interlayer. , 2019, , .		3
25	Electrical characterization of solar-blind deep-ultraviolet (Al _{0.28} Ga _{0.72}) ₂ O ₃ Schottky photodetectors grown on silicon by pulsed laser deposition. , 2019, , .		3
26	Deep-Ultraviolet Î²-Ga ₂ O ₃ Photodetectors Grown on MgO Substrates with a TiN Template. , 2019, , .		1
27	Heteroepitaxial Î²-Ga ₂ O ₃ on Conductive Ceramic Templates: Toward Ultrahigh Gain Deepâ€“Ultraviolet Photodetection (Adv. Mater. Technol. 9/2021). Advanced Materials Technologies, 2021, 6, 2170052.	5.8	0